

ABSTRACT

An etching method includes: providing, within a chamber, a substrate that includes at least a silicon-containing material and a molybdenum film or a tungsten film which is in an exposed state, and selectively etching the molybdenum film or the tungsten film relative to the silicon-containing material by supplying, into the chamber, an oxidation gas and a hexafluoride gas as an etching gas.

[Fig. 1]